

RJK1021DPE

N-Channel Power MOSFET High-Speed Switching Use

REJ03G1630-0100 Rev.1.00 Apr 03, 2008

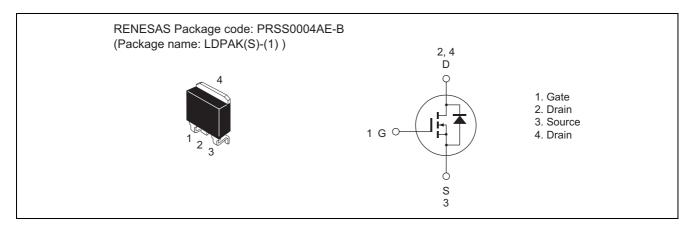
Features

• V_{DSS}: 100 V

• $R_{DS(on)}$: 20 m Ω (Max)

• I_D: 70 A

Outline



Application

• Motor control, Lighting control, Solenoid control, DC-DC converter, etc.

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Ratings | Unit | |
|---|-------------------------|-------------|------|--|
| Drain to source voltage | V_{DSS} | 100 | V | |
| Gate to source voltage | V_{GSS} | ±20 | V | |
| Drain current | I _D | 70 | А | |
| Drain peak current | I _{D (pulse)} | 140 | А | |
| Body-drain diode reverse drain current | I_{DR} | 70 | Α | |
| Body-drain diode reverse drain peak current | I _{DR (pulse)} | 140 | А | |
| Avalanche current | I _{AP} Note2 | 35 | А | |
| Channel dissipation | Pch Note1 | 100 | W | |
| Channel to case thermal impedance | θch-c | 1.25 | °C/W | |
| Channel temperature | Tch | 150 | °C | |
| Storage temperature | Tstg | -55 to +150 | °C | |

Notes: 1. Value at Tc = 25°C

2. STch = 25°C, Tch \leq 150°C, L = 100 μH

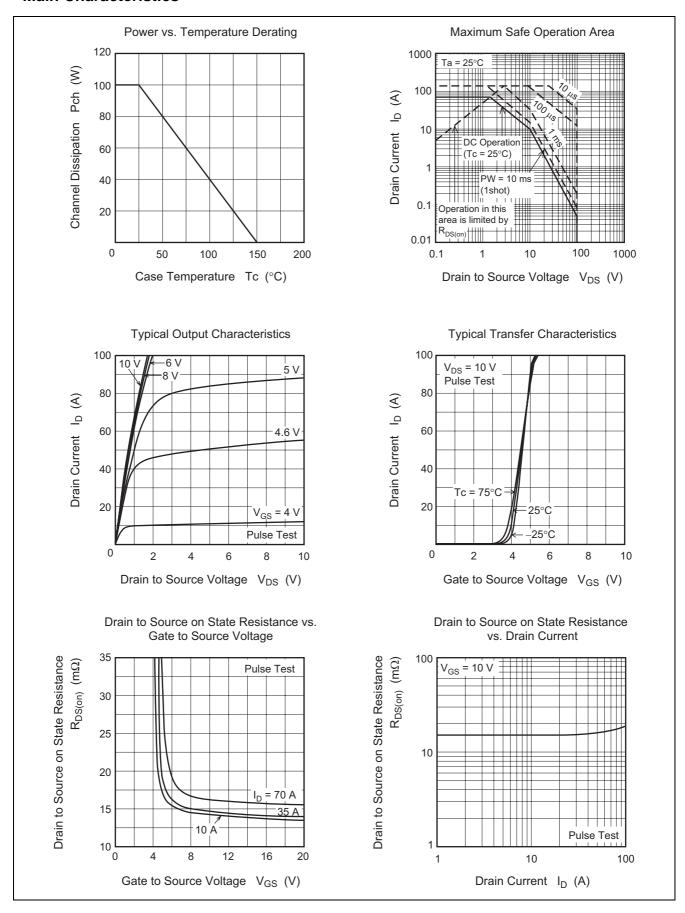
Electrical Characteristics

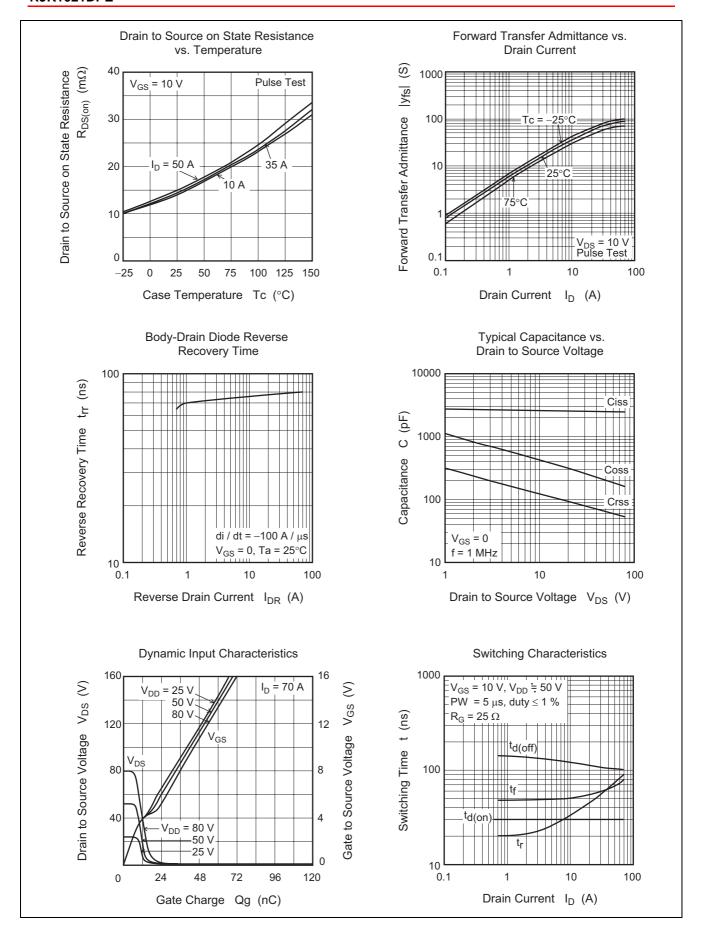
 $(Ta = 25^{\circ}C)$

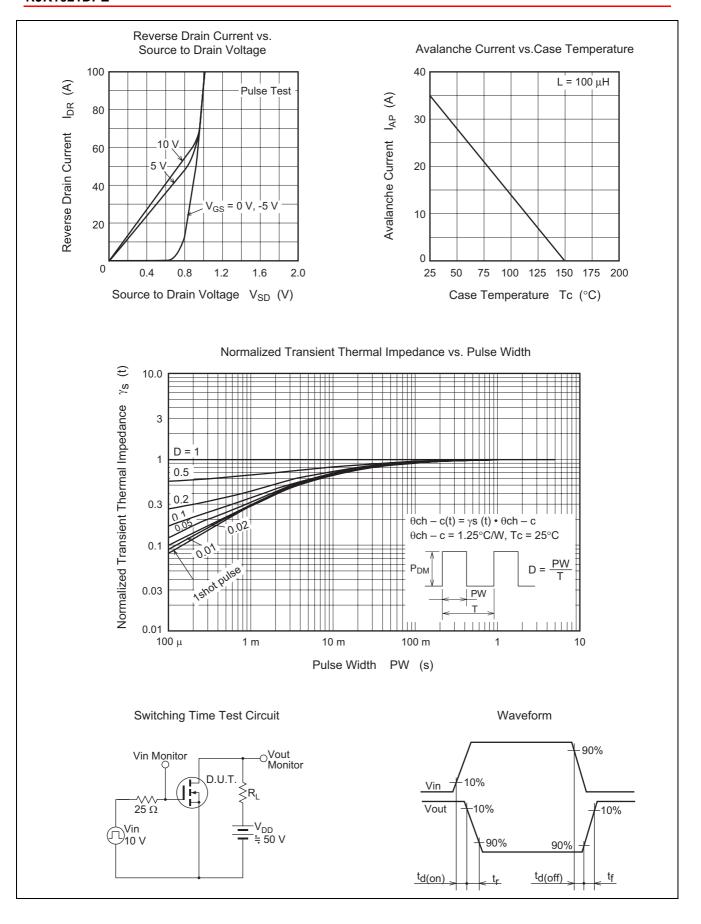
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|---|---------------------|-----|------|------|------|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 100 | _ | _ | V | $I_D = 1 \text{ mA}, V_{GS} = 0$ |
| Zero gate voltage drain current | I _{DSS} | _ | _ | 100 | μΑ | $V_{DS} = 100 \text{ V}, V_{GS} = 0$ |
| Gate to source leak current | I _{GSS} | _ | _ | ±0.1 | μΑ | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 2.0 | 3.0 | 4.0 | V | $I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note3}}$ |
| Static drain to source on state voltage | $V_{DS(on)}$ | _ | 0.56 | 0.70 | V | $I_D = 35 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$ |
| Static drain to source on state | R _{DS(on)} | _ | 16 | 20 | mΩ | $I_D = 35 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$ |
| resistance | | | | | | |
| Input capacitance | Ciss | _ | 2600 | _ | pF | V _{DS} = 10 V |
| Output capacitance | Coss | _ | 430 | | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | Crss | _ | 160 | _ | pF | f = 1 MHz |
| Turn-on delay time | t _{d(on)} | _ | 30 | _ | ns | V _{DD} = 50 V |
| Rise time | t _r | _ | 70 | _ | ns | I _D = 35 A |
| Turn-off delay time | t _{d(off)} | _ | 110 | _ | ns | $V_{GS} = 10 \text{ V}$ |
| Fall time | t _f | _ | 65 | _ | ns | $R_G = 25 \Omega$ |
| Body-drain diode forward voltage | V_{DF} | _ | 0.9 | 1.5 | V | I _F = 35 A, V _{GS} = 0 |
| Body-drain diode reverse recovery time | t _{rr} | _ | 80 | _ | ns | $I_F = 70 \text{ A}, V_{GS} = 0$ |
| | | | | | | $di_F/dt = 100 \text{ A/}\mu\text{s}$ |

Notes: 3. Pulse test

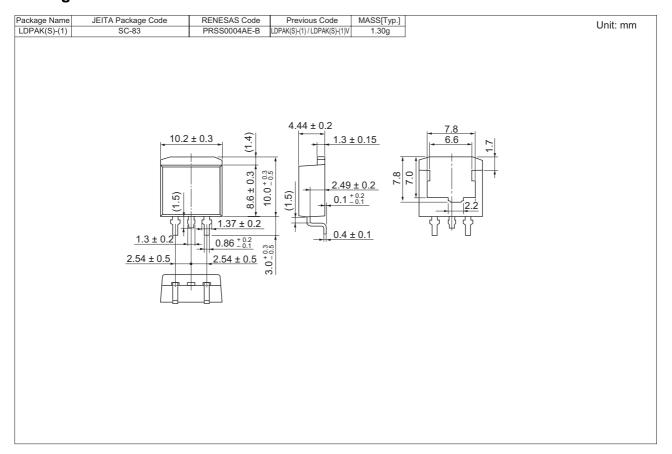
Main Characteristics







Package Dimensions



Ordering Information

| Part No. | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK1021DPE-00-J3 | 1000 pcs | Taping |

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